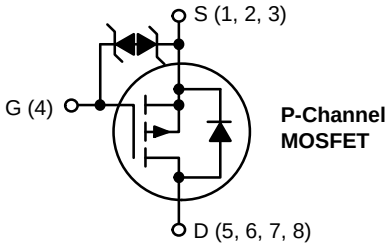
MOSFET – Power, Single, P-Channel, µ8FL

-30 V, 7.5 mΩ

NTTFS015P03P8Z

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D
−30 V	7.5 mΩ @ −10 V	−47.6 A
	12 mΩ @ −4.5 V	



Features

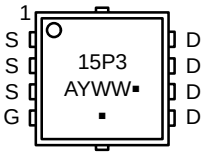
- Ultra Low $R_{DS(on)}$ to Improve System Efficiency
- Advanced Package Technology in 3.3x3.3 mm for Space Saving and Excellent Thermal Conduction
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Power Load Switch
- Protection: Reverse Current, Over Voltage, and Reverse Negative Voltage
- Battery Management

WDFN8
(µ8FL)
CASE 511AB

MARKING DIAGRAM



15P3 = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

MAXIMUM RATINGS (T_J = 25 °C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	−30	V
Gate-to-Source Voltage			V_{GS}	±25	V
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 2)	Steady State	T_C = 25 °C	I_D	−47.6	A
		T_C = 85 °C		−34.4	
Power Dissipation $R_{\theta JC}$ (Notes 1, 2)		T_C = 25 °C	P_D	33.8	W
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	Steady State	T_A = 25 °C	I_D	−13.4	A
		T_A = 85 °C		−9.6	
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)		T_A = 25 °C	P_D	2.66	W
Pulsed Drain Current	T_A = 25 °C, t_p = 10 µs		I_{DM}	−195	A
Operating Junction and Storage Temperature			T_J, T_{stg}	−55 to 150	°C
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case − Steady State (Drain) (Note 2)	$R_{\theta JC}$	3.7	°C/W
Junction-to-Ambient − Steady State (Note 2)	$R_{\theta JA}$	47	°C/W

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 1 in^2, 2 oz. Cu pad. Assuming a 76mm x 76mm x 1.6mm board.

ORDERING INFORMATION

Device	Package	Shipping†
NTTFS015P03P8ZTAG	WDFN8 (Pb-Free)	1500 / Tape & Reel
NTTFS015P03P8ZTWG	WDFN8 (Pb-Free)	3000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_J = 25 °C unless otherwise noted)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = −250 μA		−30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	I_D = −250 μA, ref to 25 °C			−4.4		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = −24 V	T_J = 25 °C			−1.0	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±25 V				±10	μA
ON CHARACTERISTICS (Note 3)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = −250 μA		−1.0		−3.0	V
Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	I_D = −250 μA, ref to 25 °C			5.6		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	V_{GS} = −10 V, I_D = −12 A			5.0	7.5	mΩ
		V_{GS} = −4.5 V, I_D = −10 A			8.0	12	
Froward Transconductance	g_{FS}	V_{DS} = −5 V, I_D = −10 A			77		S
CHARGES AND CAPACITANCES							
Input Capacitance	C_{iss}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = −15 V			2706		pF
Output Capacitance	C_{oss}				907		
Reverse Transfer Capacitance	C_{rss}				875		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = −4.5 V, V_{DS} = −15 V, I_D = −10 A			37		nC
Threshold Gate Charge	$Q_{G(TH)}$				5.1		
Gate-to-Source Charge	Q_{GS}				8.2		
Gate-to-Drain Charge	Q_{GD}				21.7		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = −10 V, V_{DS} = −15 V, I_D = −10 A			62.3	105	
SWITCHING CHARACTERISTICS, V_{GS} = 4.5 V (Note 3)							
Turn-On Delay Time	$t_{d(on)}$	V_{GS} = −4.5 V, V_{DS} = −15 V, I_D = −10 A, R_G = 6 Ω			25		ns
Rise Time	t_r				138		
Turn-Off Delay Time	$t_{d(off)}$				55		
Fall Time	t_f				98		
SWITCHING CHARACTERISTICS, V_{GS} = 10 V (Note 3)							
Turn-On Delay Time	$t_{d(on)}$	V_{GS} = −10 V, V_{DS} = −15 V, I_D = −10 A, R_G = 6 Ω			17		ns
Rise Time	t_r				34		
Turn-Off Delay Time	$t_{d(off)}$				99		
Fall Time	t_f				97		
DRAIN-SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = −10 A	T_J = 25 °C		−0.8	−1.3	V
			T_J = 125 °C		−0.65		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dI_S/dt = 100 A/μs, I_S = −10 A			40.7		ns
Charge Time	t_a				18.4		
Discharge Time	t_b				22.3		
Reverse Recovery Charge	Q_{RR}				29		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

TYPICAL CHARACTERISTICS

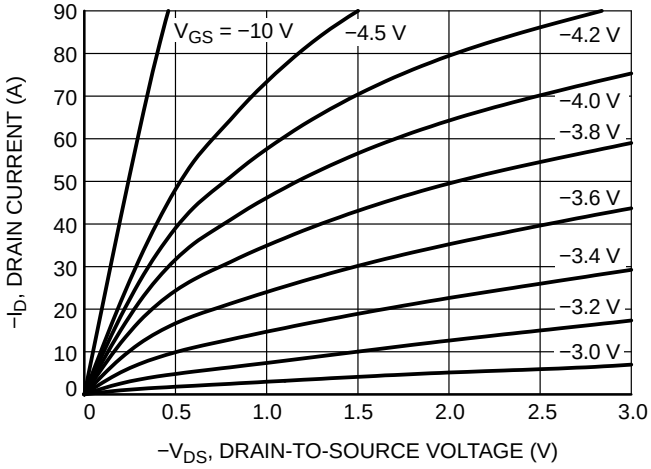


Figure 1. On-Region Characteristics

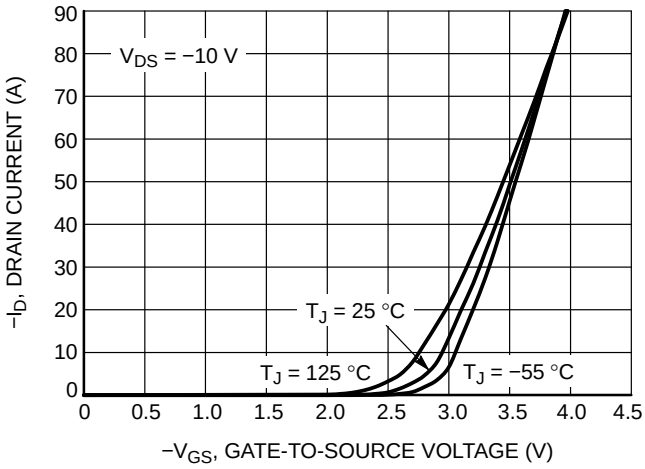


Figure 2. Transfer Characteristics

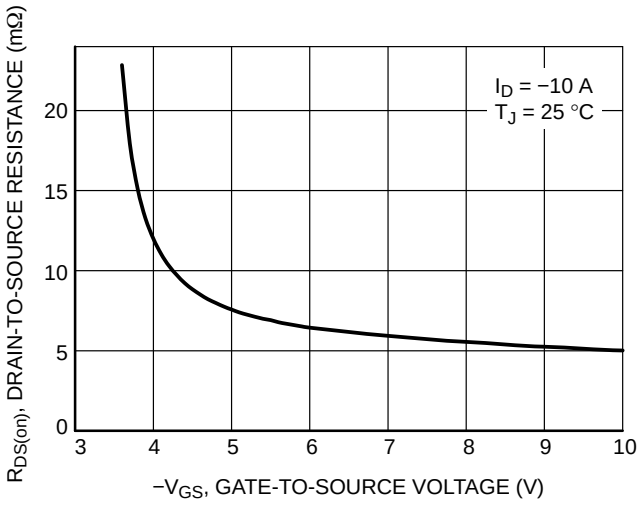


Figure 3. On-Resistance vs. Gate-to-Source Voltage

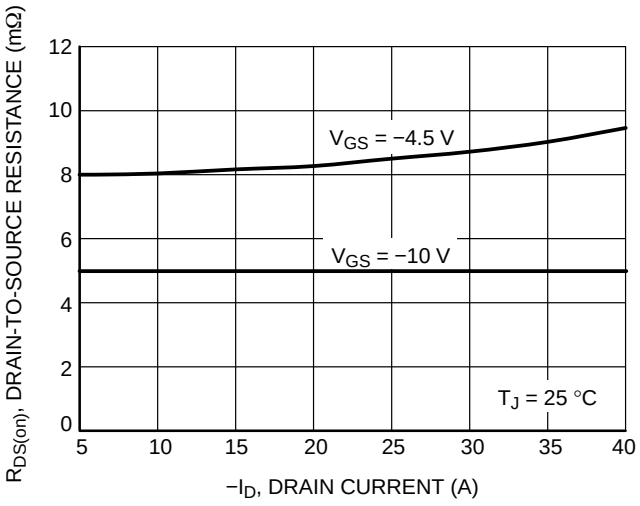


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

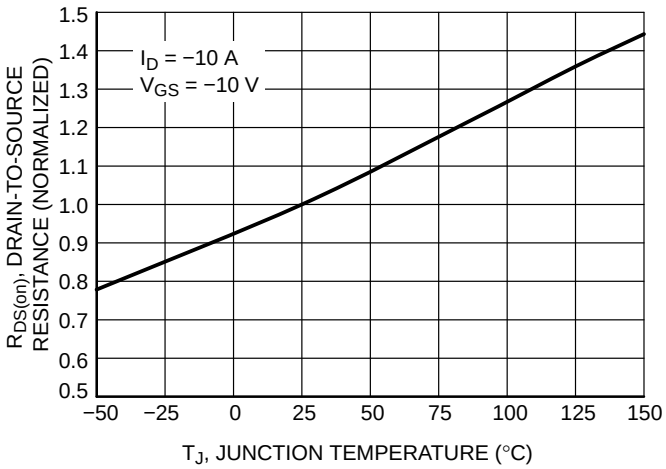


Figure 5. On-Resistance Variation with Temperature

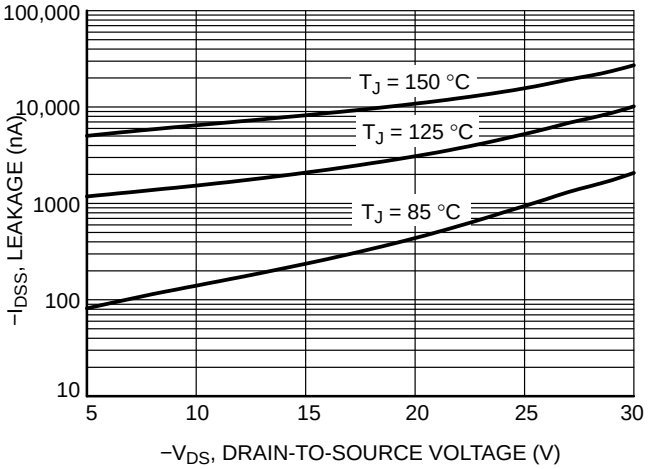


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

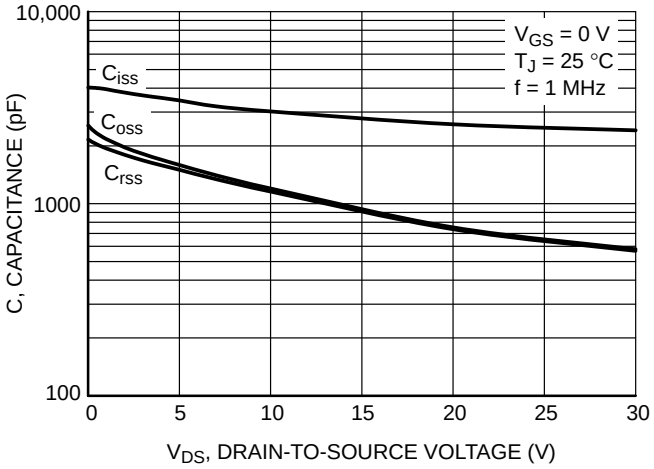


Figure 7. Capacitance Variation

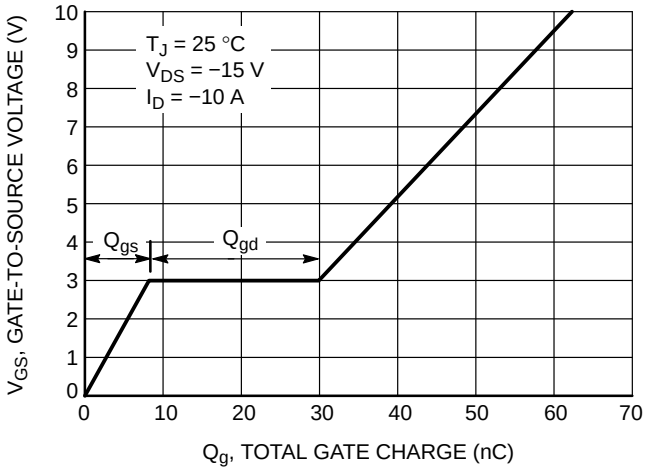


Figure 8. Gate-to-Source vs. Total Charge

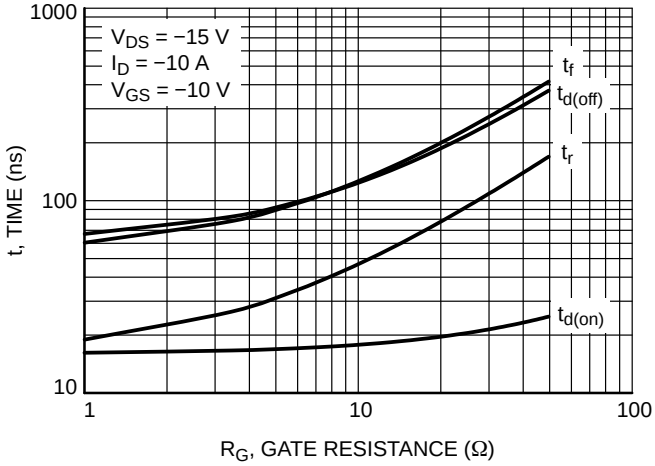


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

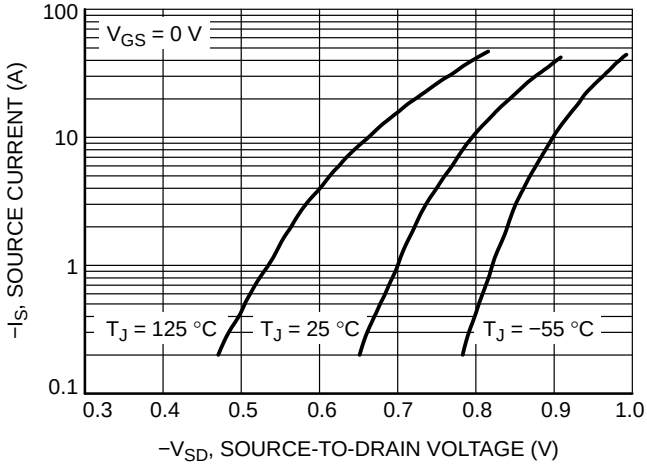


Figure 10. Diode Forward Voltage vs. Current

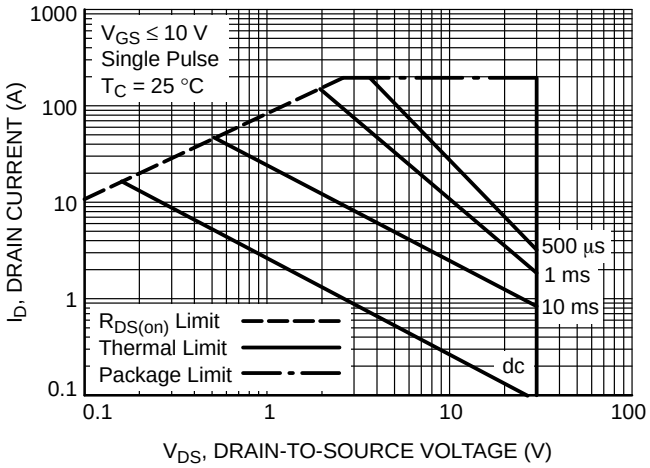


Figure 11. Maximum Rated Forward Biased Safe Operating Area

TYPICAL CHARACTERISTICS

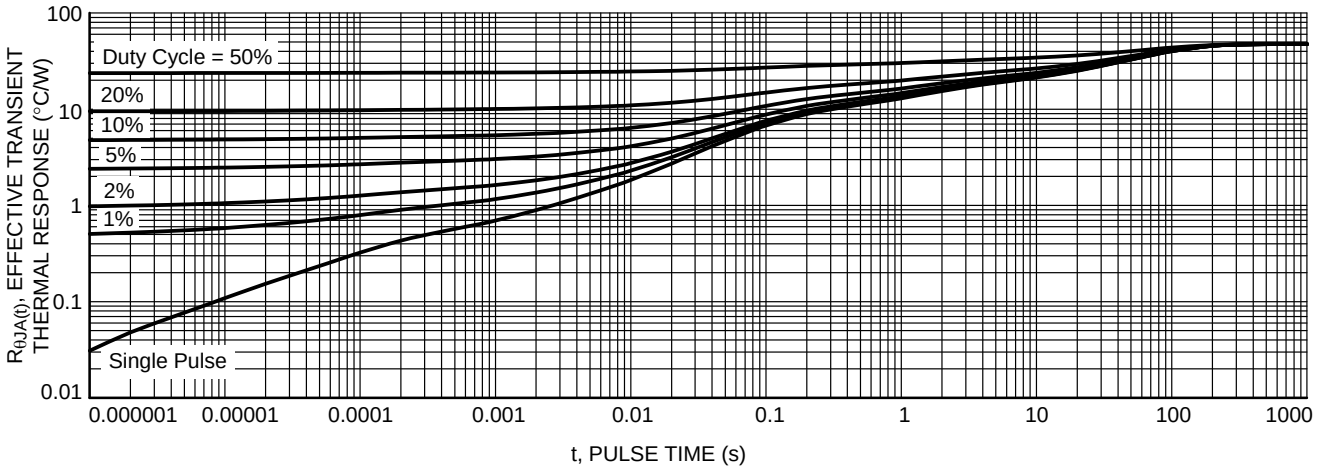


Figure 12. Thermal Response

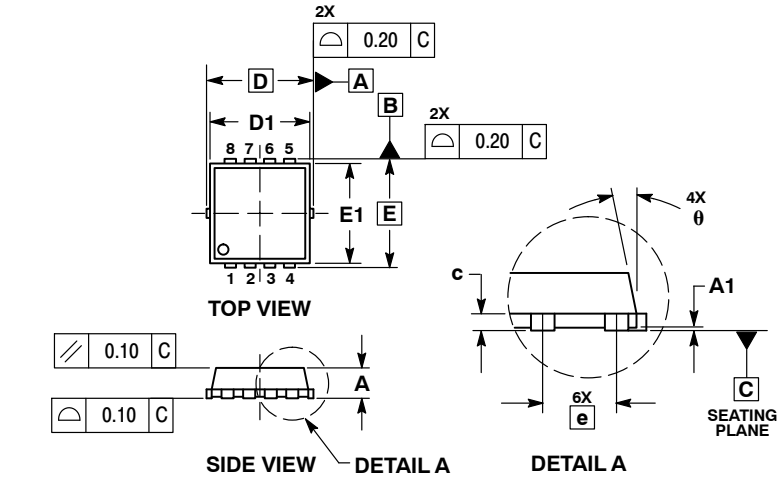
REVISION HISTORY

Revision	Description of Changes	Date
0	Initial Production Data Sheet release.	2/20/2019
1	Rebranded the Data Sheet to **onsemi** format.	10/20/2025

SCALE 2:1

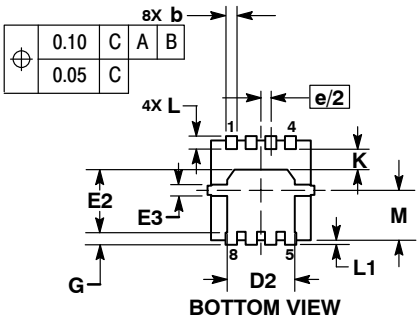
WDFN8 3.3x3.3, 0.65P
CASE 511AB
ISSUE D

DATE 23 APR 2012



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.75	0.80	0.028	0.030	0.031
A1	0.00	---	0.05	0.000	---	0.002
b	0.23	0.30	0.40	0.009	0.012	0.016
c	0.15	0.20	0.25	0.006	0.008	0.010
D	3.30 BSC			0.130 BSC		
D1	2.95	3.05	3.15	0.116	0.120	0.124
D2	1.98	2.11	2.24	0.078	0.083	0.088
E	3.30 BSC			0.130 BSC		
E1	2.95	3.05	3.15	0.116	0.120	0.124
E2	1.47	1.60	1.73	0.058	0.063	0.068
E3	0.23	0.30	0.40	0.009	0.012	0.016
e	0.65 BSC			0.026 BSC		
G	0.30	0.41	0.51	0.012	0.016	0.020
K	0.65	0.80	0.95	0.026	0.032	0.037
L	0.30	0.43	0.56	0.012	0.017	0.022
L1	0.06	0.13	0.20	0.002	0.005	0.008
M	1.40	1.50	1.60	0.055	0.059	0.063
θ	0 °	---	12 °	0 °	---	12 °

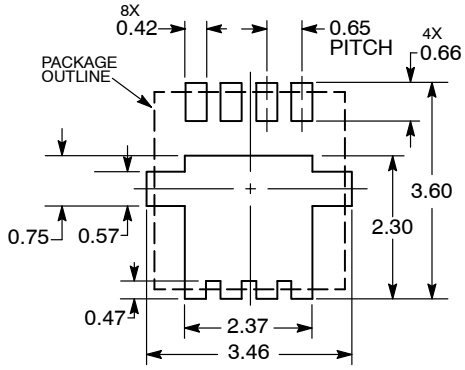


GENERIC MARKING DIAGRAM*

XXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

SOLDERING FOOTPRINT*



DIMENSION: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	**98AON30561E**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	**WDFN8 3.3X3.3, 0.65P**	**PAGE 1 OF 1**

ADDITIONAL INFORMATION

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